

U423 HIGH INPUT IMPEDANCE MONOLITHIC DUAL N-CHANNEL JFET



Linear Systems replaces discontinued Siliconix U423

The U423 is a high input impedance Monolithic Dual N-Channel JFET

The U423 monolithic dual n-channel JFET is designed to provide very high input impedance for differential amplification and impedance matching. Among its many unique features, this series offers operating gate current specified at -250 fA. The U423 is a direct replacement for discontinued Siliconix U423.

The 6 Pin SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

U423 Applications:

- Ultra Low Input Current Differential Amps
- High-Speed Comparators
- Impedance Converters

FEATURES							
HIGH INPUT IMPED	HIGH INPUT IMPEDANCE			I _G = 0.25pA MAX			
HIGH GAIN		gfs = 120μmho MIN					
LOW POWER OPER	ATION	V _{GS(OFF)} =	(OFF) = 2V MAX				
ABSOLUTE MAXIMUM RATINGS							
@ 25°C (unless otherwise noted)							
Maximum Temperatures							
Storage Temperatu	-65	-65°C to +150°C					
Operating Junction	+15	+150°C					
Maximum Voltage and Current for Each Transistor – Note 1							
-V _{GSS} Gate	Voltage to Drain or So	40\	40V				
-V _{DSO} Drain	to Source Voltage	40\	40V				
-I _{G(f)} Gate	-I _{G(f)} Gate Forward Current						
Maximum Power Dissipation							
Device Dissipation @ Free Air – Total 400mW @ +125°C							
MATCHING CHARACTERISTICS @ 25°C UNLESS OTHERWISE NOTED							
SYMBOL	CHARACTERISTICS	VALUE	UNITS	CONDITIONS			
$ \Delta V_{GS1-2}/\Delta T $ max.	DRIFT VS.	40	μV/°C	V_{DG} =10V, I_{D} =30 μ A			
	TEMPERATURE			T _A =-55°C to +125°C			
V _{GS1-2} max.	OFFSET VOLTAGE	25	mV	V_{DG} =10V, I_{D} =30 μ A			
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ELECTRICAL CH	ARACTERISTICS @ 25 C (unless of	otnerwise noted)
SVMBOL	CHARACTERISTICS	MIN	

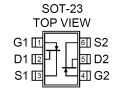
BV _{GSS} Breakdown Voltage 40 60 V V _{DS} = 0 I _G = InA	SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
Transconductance Full Conduction 300 1500 μmho V _{DS} =10V V _{DS} =0V f=1kHz	BV _{GSS}	Breakdown Voltage	40	60		V	$V_{DS} = 0$ $I_G = 1nA$
TRANSCONDUCTANCE Full Conduction 300 1500 μmho V _{DS} = 10V V _{GS} = 0V f = 1kHz	BV_{GGO}	Gate-To-Gate Breakdown	40			V	$I_{G} = 1\mu A$ $I_{D} = 0$ $I_{S} = 0$
DRAIN CURRENT Full-Conduction 60 1000 μA V _{DS} = 10V V _{GS} = 0V					1500	μmho	
I _{DSS} Full-Conduction Full-Conduction	Y _{fS}	Typica <mark>l O</mark> per <mark>at</mark> ion	12 0	200	350	μmho	$V_{DG} = 10V$ $I_D = 30\mu A$ $f = 1kHz$
Vosioff Pinchoff voltage 2.0 V Vos = 10V Io = 1nA	I _{DSS}	Full-Conduction	60		1000	μΑ	$V_{DS} = 10V$ $V_{GS} = 0V$
VGS Operating Range 1.8 V VDG = 10V ID = 30μA Igmax. Operating 25 pA VDG = 10V ID = 30μA -Igmax. High Temperature 250 pA TA = +125°C ID = 30μA Igss max. At Full Conduction 1.0 pA VDG = 0V VGS = 20V -Igss max. High Temperature 1.0 nA TA = +125°C D OUTPUT CONDUCTANCE 1.0 nA TA = +125°C D Yoss Operating 10 μmho VDS = 10V VGS = 0V Yos Operating 10 μmho VDS = 10V ID = 30μA CMR COMMON MODE REJECTION -20 log ΔV GS1-2/ ΔVDS 90 dB ΔVDS = 10 to 20V ID = 30μA NF Figure 90 dB ΔVDS = 10V	V _{GS(off)}				2.0	V	V _{DS} = 10V
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$					1.8	V	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	- 65						50 5 1
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _G max.	Operating			.25	pA	$V_{DG} = 10V$ $I_{D} = 30\mu A$
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	-l _G max.	High Temperature			250	pА	T _A = +125°C
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I _{GSS} max.	At Full Conduction	-	-	1.0	pA	$V_{DS} = 0V$ $V_{GS} = 20V$
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	-I _{GSS} max.	High Temperature	-	-	1.0	nA	T _A = +125°C
$ \begin{array}{ c c c c c c c c c } \hline Y_{OS} & Operating & & 0.1 & 3.0 & \mu mho & V_{DG} = 10V & I_D = 30 \mu A \\ \hline \hline COMMON MODE REJECTION & & & & & & & & \\ \hline -20 \log \Delta V_{GS1-2}/\Delta V_{DS} & & 90 & & dB & \Delta V_{DS} = 10 to 20V & I_D = 30 \mu A \\ \hline -20 \log \Delta V_{GS1-2}/\Delta V_{DS} & & 90 & & dB & \Delta V_{DS} = 5 to 10V & I_D = 30 \mu A \\ \hline NOISE & & & & & & & & & \\ NF & Figure & & & 1 & dB & & & & & & \\ Figure & & & 1 & dB & & & & & & \\ \hline e_n & Voltage & & 20 & 70 & nV/VHz & V_{DG} = 10V & I_D = 30 \mu A & f = 10Hz \\ \hline & & & & & & & & & & & \\ \hline CAPACITANCE & & & & & & & & \\ \hline \end{array} $	v				10	umbo	V = 10V V = 0V
$ \begin{array}{ c c c c c c c c } \hline CMR & \begin{array}{ c c c c c c c c } \hline \textbf{COMMON MODE REJECTION} \\ \hline -20 \log \Delta V_{GS1-2}/\Delta V_{DS} & & 90 & & dB & \Delta V_{DS} = 10 \text{ to } 20V & I_D = 30 \mu A \\ \hline -20 \log \Delta V_{GS1-2}/\Delta V_{DS} & & 90 & & dB & \Delta V_{DS} = 5 \text{ to } 10V & I_D = 30 \mu A \\ \hline \hline \textbf{NF} & \begin{array}{ c c c c c } \hline \textbf{NOISE} & & & & & & & & & & & & & & & & & & &$						'	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	TOS	1 0		0.1	3.0	μιτιιο	V _{DG} - 10V I _D - 30μA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	CMR	-20 log ΔV _{GS1-2} / ΔV _{DS}				dB	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		-20 log ΔV _{GS1-2} / ΔV _{DS}		90		dB	$\Delta V_{DS} = 5 \text{ to } 10V$ $I_D = 30 \mu A$
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$							5 , 5
10 V _{DG} = 10V I _D = 30μA f = 1KHz <u>CAPACITANCE</u>	NF	Figure			1	_	· ·
<u>CAPACITANCE</u>	e_n	Voltage		20	70	nV/√Hz	5 1
				10			$V_{DG} = 10V I_{D} = 30\mu A f = 1KHz$
$I = I_{SS}$ III I_{SS} I	C				3.0	nF.	V = 10V V = 0 f = 1MHz
C _{RSS} Reverse Transfer 1.5 pF		•				·	DS- 104 ACS- 0 1 - 1141115

Available Packages:

LSU423 in SOT-23

LSU423 available as bare die Please contact Micross for full package and die dimensions

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